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Fuxi Gan
Lisong Hou
Editors

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Introduction

The Fifth International Symposium on Optical Storage was held 22–26 May 2000 in Shanghai-Pudong, People's Republic of China, under the auspices of National Natural Science Foundation of China, Chinese Society for Optical Storage, China Optical Disk Manufacturer's Association, and SPIE—The International Society for Optical Engineering. The symposium was organized by Shanghai Institute of Optics and Fine Mechanics (SIOFM), Chinese Academy of Sciences (CAS), and Tsinghua University. The four previous symposia in this series were held in Shanghai-Jiading (1988), Chongqing (1990), Kunming (1992), and Shenzhen (1996), respectively, and they have continued to grow over the years. More than 120 scientists, technologists, and experts from universities, research institutes, and industries of 12 countries and regions participated in the fifth symposium, which provided a forum for reviewing recent progress and exchanging information in a wide range of topics including materials, physics, media, drive, and measurement technologies in optical storage. This forum promoted discussion on both the theoretical aspects and practical applications of optical storage, and strengthened cooperation and friendship within the optical storage community.

Eighty-four papers were presented at the symposium, including forty-eight as oral presentations in seven technical sessions and thirty-six as posters. From these papers, invited and contributed, oral and poster, it can be seen that interest in high-density and high-data-rate optical storage has become a dominant trend. Materials, technologies, components, and devices for HD-DVD (high-density DVD) have been attracting more and more research and development activities apart from the digital versatile disk (DVD) technology. Certainly, some new mechanisms, materials, and formats for optical storage have emerged. But due to the limitation of space, not all the presented papers can be published in this volume. The 69 papers published here cover the development and challenge of optical storage, magneto-optical, phase-change, and organic media, disk manufacturing technology, mastering, drive, testing, and applications, as well as high-density optical storage.

We are very grateful to the members of the International Advisory Committee, the Organizing Committee, and the Program Committee, as well as the session chairs for their fruitful work in the preparation and operation of the symposium. Thanks are also extended to our invited speakers and all of the contributing authors for their elaborate preparation of abstracts for the advance program and manuscripts for these proceedings. We also gratefully acknowledge the sponsors and cosponsors, domestic and abroad, without whose support we could not have held such a successful symposium.

Fuxi Gan

Contents

ix	<i>Symposium Committees</i>
xi	<i>Introduction</i>

PART 1 DEVELOPMENT AND CHALLENGE OF OPTICAL STORAGE

1	Superhigh-density optical storage in China (Invited Paper) [4085-01] F. Gan, H. Ruan, Shanghai Institute of Optics and Fine Mechanics (China)
9	Three-dimensional digital storage technology (Invited Paper) [4085-02] D. Xu, L. Ma, Tsinghua Univ. (China)
15	New developments in optical phase-change memory (Invited Paper) [4085-03] S. R. Ovshinsky, W. Czubytyj, Energy Conversion Devices, Inc. (USA)
23	3.5-in. MO as a technology of choice for the 21st century: from text document to digital motion picture (Invited Paper) [4085-04] K. Ogawa, S. Moroto, Fujitsu Ltd. (Japan); K. Itho, K. Shono, S. Ogawa, Fujitsu Labs. Ltd. (Japan)
28	Breakthrough and the future phase-change optical disk technology (Invited Paper) [4085-05] T. Ohta, Matsushita Electric Industrial Co., Ltd. (Japan)
36	Recent progress of superresolution near-field structure (Super-RENS) (Invited Paper) [4085-06] J. Tominaga, T. Nakano, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
40	Challenge of terabyte optical recording (Invited Paper) [4085-07] T. C. Chong, B. Xu, Data Storage Institute/National Univ. of Singapore
46	Holographic properties of doped stoichiometric LiNbO₃ crystals [4085-08] S. Tao, Beijing Polytechnic Univ. (China); M. Lee, K. Kitamura, National Institute for Research in Inorganic Materials (Japan); H. Hatano, Pioneer Corp. (Japan); L. Galambos, L. Hesselink, Stanford Univ. (USA)

PART 2 MO OPTICAL STORAGE

51	Advanced MO disk and its application to a digital camera (Invited Paper) [4085-09] K. Shimazaki, S. Ohnuki, Hitachi Maxell Ltd. (Japan); H. Terasaki, Y. Suzuki, Sanyo Electric Co., Ltd. (Japan); Y. Nakajima, Y. Yoda, Olympus Optical Co., Ltd. (Japan)
56	Dependence of magneto-optical properties on dimensional factors for Co/Pt multilayers recording media [4085-10] Y. Zhang, H. Li, H. Zhao, Kunming Institute of Precious Metals (China)

- 64 **Temperature dependence of magnetic and magneto-optical properties in Sm(Tb,Dy)FeCo thin films [4085-11]**
Z. Li, K. Wang, Y. Hu, Huazhong Univ. of Science and Technology (China); R. Xiong, Wuhan Univ. (China); X. Wang, X. Yang, Huazhong Univ. of Science and Technology (China)
- 68 **Magnetic and magneto-optical properties of Pt-Co thin films prepared by using composite and alloy targets [4085-12]**
D. Shen, B. Ma, K. Xun, M. Li, Shanghai Institute of Metallurgy (China)
- 72 **Thermal stability in magneto-optical recording media: analysis of magnetization decay [4085-13]**
R. Sbiaa, M. Mochida, Y. Itoh, T. Suzuki, Toyota Technological Institute (Japan)
- 76 **Magneto-optical and optical properties of GdFe films [4085-14]**
Z. Shen, J. Li, S. Wang, S. Zhou, L. Chen, Fudan Univ. (China)
- 80 **Novel measuring system for mechanical characteristics of optical disks [4085-15]**
H. Wang, X. Pei, C. Xie, B. Liu, Huazhong Univ. of Science and Technology (China)
- 84 **Influence of AlN coverlayers prepared by reactive sputtering on DyFeCo magneto-optical media [4085-16]**
R. Xiong, Wuhan Univ. (China) and Huazhong Univ. of Science and Technology (China); Z. Li, X. Yang, Huazhong Univ. of Science and Technology (China); D. Tian, J. Shi, W. Tang, Wuhan Univ. (China)
- 88 **Measurement system for the fatigue behavior of magneto-optical recording films [4085-17]**
Z. Li, K. Wang, L. Tan, X. Yang, Z. Hu, Huazhong Univ. of Science and Technology (China)
- 92 **Optimization of the structure of magneto-optical disk via genetic algorithms [4085-18]**
X. Yang, Z. Li, Z. Peng, K. Wang, Huazhong Univ. of Science and Technology (China)

PART 3 PHASE-CHANGE OPTICAL STORAGE

- 96 **Zn-Ga-In oxide films for high-density DVD-R with blue laser (Invited Paper) [4085-19]**
M. Okuda, Okuda Technical Office (Japan); T. Aoki, A. Suzuki, T. Matsushita, Osaka Sangyo Univ. (Japan)
- 104 **Computer simulation with spreadsheet to analyze crystalline structure in phase-change recording layer by fractal theory [4085-20]**
S. Usuda, Osaka Prefectural College of Technology (Japan); M. Okuda, Okuda Technical Office (Japan)
- 108 **Reliability test for phase-change optical recording media [4085-21]**
Y. Okino, Kansai Univ. (Japan); T. Kubo, Hiroshima International Univ. (Japan); M. Okuda, Okuda Technical Office (Japan); S. Hasegawa, Sizuoka Univ. (Japan)
- 112 **Effects of preparation parameters on the optical constants of Ge₂Sb₂Te₃ thin films [4085-22]**
Q. Xie, Shanghai Institute of Optics and Fine Mechanics (China) and Changsha Communications Univ. (China); L. Hou, H. Ruan, J. Li, J. Li, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)

- 117 **Effects of thermal treatment on the optical constants of GeTe, Sb₂Te₃, Ge₂Sb₂Te₅ systems** [4085-23]
Q. Xie, Shanghai Institute of Optics and Fine Mechanics (China) and Changsha Communications Univ. (China); L. Hou, H. Ruan, J. Li, J. Li, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 121 **Thermochromic thin film and its application in optical data storage** [4085-24]
Q. Chen, J. Tominaga, T. Fukaya, L. Q. Men, T. Nakano, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
- 125 **Effects of sputtering parameters on the optical properties of AgInSbTe phase-change film** [4085-25]
J. Li, L. Hou, H. Ruan, Q. Xie, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 129 **Effects of film thickness on the optical properties of AgInSbTe phase-change films** [4085-26]
J. Li, L. Hou, H. Ruan, Q. Xie, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 133 **Optical properties and static recording performances of Ag-In-Te-Sb-O films using short-wavelength laser** [4085-27]
Q. Li, L. Hou, J. Li, Q. Xie, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China); N. Liu, Shandong Univ. of Science and Technology (China)
- 137 **Thickness error analysis of multilayers for recordable and phase-change optical disks** [4085-28]
Y. Wang, D. Gu, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 142 **Initializer for phase-change optical media** [4085-29]
Y. Okino, S. Nakahara, Kansai Univ. (Japan); M. Takita, Takita Research and Development Co., Ltd. (Japan)

PART 4 OPTICAL STORAGE USING ORGANIC MATERIALS

- 146 **Optical writing and erasing properties of phthalocyanine zinc spin-coated films** [4085-30]
J. Yin, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 150 **Metallized thiazolylazo dyes for short-wavelength optical recording media** [4085-31]
S. Wang, S. Shen, H. Xu, Institute of Photographic Chemistry (China); D. Gu, J. Yin, X. Dong, Shanghai Institute of Optics and Fine Mechanics (China)
- 154 **Spectral and optical properties of a new subphthalocyanine dye as a potential optical recording material** [4085-32]
Y. Wang, D. Gu, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 158 **Novel nondestructive readout method for rewritable storage systems of diarylethene photochromic molecules** [4085-33]
H. Guo, F. Zhang, Y. Tang, F. Zhao, G. Wu, Tsinghua Univ. (China)
- 162 **Properties of a cyanine dye for high-density digital versatile disk recording (DVD-R)** [4085-34]
X. Dong, F. Gan, D. Gu, F. Tang, J. Yin, Shanghai Institute of Optics and Fine Mechanics (China)

- 167 **Two-photon bit data storage in azobenzene polymer liquid crystal using low-power cw laser** [4085-35]
J. Zhang, Z. Liang, H. Ming, Y. Xia, Y. Long, J. Xie, Q. Zhang, W. Shen, Univ. of Science and Technology of China
- 171 **Novel bisthiénylene-based photochromic material for optical storage** [4085-36]
H. Tu, H. Tian, East China Univ. of Science and Technology
- 176 **Synthesis and spectral properties of axially bromo-substituted subphthalocyanines for optical storage** [4085-37]
H. Tu, H. Tian, East China Univ. of Science and Technology

PART 5 HIGH-DENSITY OPTICAL STORAGE

- 181 **Blue laser and high-numerical-aperture optical disk system for digital video recording (DVR) (Invited Paper)** [4085-38]
H. van Houten, Philips Research Labs. (Netherlands)
- 191 **Further advances in electron beam recording** [4085-39]
G. Cartwright, G. Reynolds, C. Baylis, A. Pearce, S. Swann, C. Dix, N. Ogilvie, Nimbus Technology and Engineering Ltd. (UK)
- 197 **Nanometer-scale optical switch formation in antimony thin film and its time response property** [4085-40]
T. Fukaya, J. Tominaga, T. Nakano, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
- 201 **Angular dependence of near-field scattering light from superresolution near-field structure disk** [4085-41]
T. Nakano, T. Gibo, L. Q. Men, National Institute for Advanced Interdisciplinary Research (Japan); H. Fuji, Sharp Corp. (Japan); J. Tominaga, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
- 204 **High-density optical data storage using scattering-mode superresolution near-field structure** [4085-42]
L. Q. Men, J. Tominaga, National Institute for Advanced Interdisciplinary Research (Japan); H. Fuji, Sharp Corp. (Japan); Q. Chen, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
- 208 **Ultrahigh-density recording based on third-order optical nonlinearities** [4085-43]
A. Rong, Beijing Univ. of Aeronautics and Astronautics (China); D. Huang, Shanghai Jiaotong Univ. (China); Q. Chen, Beijing Univ. of Aeronautics and Astronautics (China)
- 216 **Femtosecond-laser-induced recording in glass** [4085-44]
X. Jiang, C. Zhu, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 220 **Numerical simulation of electromagnetic propagation in high-data-density near-field optical recording** [4085-45]
K. Liu, H. Ming, Y. Lu, M. Bai, J. Xie, Univ. of Science and Technology of China

PART 6 TESTING AND MEASUREMENT TECHNOLOGY

- 224 **CD-R mastering and stamper quality testing [4085-46]**
G. Zhang, H. He, G. Chen, J. Sun, Q. Hu, Shanghai Institute of Optics and Fine Mechanics (China); J. Zhou, B. Gan, Y. Xu, F. Sun, Zibo Winbo Laser Disk Ltd. Co. (China)
- 228 **Applications of AFM technology in CD-R research and development [4085-47]**
J. Sun, G. Zhang, Q. Hu, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 233 **Analysis of position error signal in out-radial optical pickup systems [4085-48]**
B. Xu, T. C. Chong, M. Y. Liu, G. Yuan, Y. Lu, Data Storage Institute/National Univ. of Singapore
- 237 **Absolute time in pregroove (ATIP) test system for CD-R disks [4085-49]**
H. He, G. Zhang, Shanghai Institute of Optics and Fine Mechanics (China)
- 240 **Data analysis method of DVD disk parameters affected by replication process [4085-50]**
D. Meng, L. Pan, L. Ma, K. Ji, D. Xu, Tsinghua Univ. (China)
- 244 **Diffraction analysis of optical disk readout signal deterioration caused by decline of groove wall [4085-51]**
X. Cheng, H. Jia, D. Xu, Tsinghua Univ. (China)
- 249 **Testing system for groove geometry of CD-R substrates [4085-52]**
W. Xu, F. Gan, H. Shi, H. He, Q. Lin, J. Sun, X. Li, Shanghai Institute of Optics and Fine Mechanics (China)
- 253 **Analysis and study on measurement of jitter and its precision [4085-53]**
L. Ma, D. Xu, L. Pan, Tsinghua Univ. (China)
- 258 **Phase-shifting apodizer for next-generation DVD [4085-54]**
H. Wang, Z. Chen, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)
- 262 **Study and analysis of a new servo system in an optical disk player [4085-55]**
L. Ma, Z. Chen, D. Xu, L. Pan, Tsinghua Univ. (China)
- 267 **Using a modified repetitive control for improving optical disk tracking accuracy [4085-56]**
Z. Zhang, L. Pan, L. Ma, D. Xu, Tsinghua Univ. (China)
- 272 **Observation of microstructures on the recording films of $\text{Ag}_8\text{In}_{14}\text{Sb}_{55}\text{Te}_{23}$ and phthalocyanine by AFM [4085-57]**
J. Sun, F. Gan, Shanghai Institute of Optics and Fine Mechanics (China)

PART 7 APPLICATION AND PRODUCTION TECHNOLOGY

- 277 **Standards for 12-cm optical disks (Invited Paper) [4085-58]**
R. ten Kate, Philips Optical Disk Technology Ctr. (Netherlands)
- 283 **DVD-RAM for all audio/video, PC, and network applications (Invited Paper) [4085-59]**
I. Satoh, N. Yamada, Matsushita Electric Industrial Co., Ltd. (Japan)
- 291 **Current challenges in thin film production technology for optical disks (Invited Paper) [4085-60]**
B. Heinz, M. Dubs, S. Voser, T. Matt, G. Strasser, Balzers Ltd. (Liechtenstein)

- 298 **Developments in CD-R (Invited Paper) [4085-61]**
J. A. Th. Verhoeven, Toolex International NV (Netherlands); W. S. Mischke, Trex BV (Netherlands)
- 306 **Improvements of optical, mechanical, and geometrical properties of DVD-RAM substrate [4085-62]**
S. Moon, K. Seong, H. Kim, S. Kang, Yonsei Univ. (Korea); J.-S. Lee, D. Lee, LG Corporate Institute of Technology (Korea)
- 311 **Searching for CD-R process window for different phthalocyanine dyes [4085-63]**
H. Pu, S. Wang, Linfair Engineering Co., Ltd. (Hong Kong); K. C. M. Lee, Ciba Speciality Chemicals Ltd. (Taiwan)
- 317 **Personal optical disk library (PODL) for knowledge engineering [4085-64]**
H. Wang, H. Jia, D. Xu, Tsinghua Univ. (China)
- 322 **Antipiracy technology study on optical disks [4085-65]**
H. Li, D. Lu, D. Xu, L. Pan, Tsinghua Univ. (China)
- 327 **Eight-terabyte storage system by a new file system [4085-66]**
J. Xiong, L. Pan, J. Pei, D. Meng, Tsinghua Univ. (China)
- 332 **Novel micromachined sensor head for optical data storage applications [4085-67]**
C. Mihalcea, M. Kuwahara, J. Tominaga, N. Atoda, National Institute for Advanced Interdisciplinary Research (Japan)
- 336 **Near-line inspector of optical disk parameters [4085-68]**
D. Meng, L. Ma, L. Pan, L. Zhang, Tsinghua Univ. (China)
- 340 **Magneto-optical storage card [4085-69]**
C. Yang, Q. Fan, H. Chen, Y. Li, Univ. of Electronic Science and Technology of China
- 345 *Author Index*

Super high-density optical storage in China

Fuxi Gan, Hao Ruan*

Shanghai Institute of Optics and Fine Mechanics, Chinese Academy of Sciences

P. O. Box 800-211, Shanghai 20180, P. R. China

ABSTRACT

This paper gives a review of the new progress in the super high-density optical storage research in China. The main research fields are short wavelength optical disk storage, near field optical storage, digital holographic storage and photo-induced multi dimensional storage. General remarks of the super high-density optical storage research are also given.

Keywords: optical storage, high-density, short wavelength, near field, holographic, photo-induced, multi dimensional

1. INTRODUCTION

21st century is the Tera-bit information century. The process, transfer and storage of the Tera-bit information should possess the characteristics of super high-density and super high transfer rate. In recent years, optical storage has been a very rapid development in response to the ever-growing demands. The trend of optical storage development is from infrared recording wavelength to ultraviolet recording wavelength; from far field optical recording to near field optical recording; from 2-dimensional storage to multi dimension storage; from photo-thermal effect to photo-induced effect. The optical storage research and development were started in 1985 in China. $\phi 130$ mm magneto-optical and phase change disks and $\phi 120$ mm recordable disks were developed in 1990 and 1996, respectively. More attention has been paid into high-density optical storage recently: short wavelength (~ 500 nm) recording, near field optical recording, digital holographic recording, and photo-induced multi-dimensional storage. This paper gives a review of the new progress in the super high-density optical storage research in China.

2. SHORT WAVELENGTH OPTICAL DISK STORAGE

Chinese Academy of Sciences is conducting a super high-density optical disk storage project (HD-DVD). The objective of $\phi 120$ mm HD-DVD is 20.GB storage capacities on single side, which means the minimum mark length is about 200nm, storage density is about 10-20 Gb/in². The write/erase cycle is larger than 1000 times and data transfer rate is about 50Mb/s. The solutions include shortening laser wavelength by adopting 400~500 nm GaN lasers, enlarging numerical aperture of objective lens from 0.65 to 1.0, using super-resolution detection methods, such as optical super resolution, magnetically induced super resolution (MSR), and SUPER-RENS, shortening track pitch distance to 300~400 nm, improving encode, format, and write/read strategies, such as zone constant angular velocity (ZCAV), zone constant linear velocity (ZCLA), sampling serve (SS), mark-edge recording, land-groove recording and so on.

High-density optical storage media materials must meet a series of special requirements. Considerable work has been carried out in Chinese Academy of Sciences. Three kinds of magneto-optical materials have been studied: Pt/Co, or Pd/Co multilayer films, MnBiAl films and garnet films¹. To meet the needs of high-density information records, MO materials should have large Kerr rotation at short wavelength, large coercivity and fine grain size. The effects of doping different third elements in Co or Pt (Pd) layers are studied, such as Cu, Al, Ag, Ni, Fe². Different preparing conditions have been tried, including Ar pressure, substrate temperature, annealing temperature and time and so on³. MnBi films have been modified by doping with different elements, such as Al, Au, Ag, In, Pt, Sb, Si and RE⁴. For garnet films, the influences of doped ions have been studied, such as doping Bi to increase Faraday rotation, doping Cu or RE to increase coercivity, doping Ga, Al to increase Faraday rotation and coercivity and to reduce M_s and T_c ^{5,6}. The optimum design of disk structure such as reflective layers and thickness of garnet films has also been studied.

*Correspondence: Email: ruanhao@mail.shcnc.ac.cn; Telephone: +86-21-59534890 Ext. 582; Fax: +86-21-59528812.

Fig. 1 shows the curves of the saturated polar Kerr rotation θ_K vs. wavelength as the function of the doping concentration of Ni in the Pt spacer layer⁷. An enhanced magneto-optical effect appears in PtNi/Co multilayers at small dopings, for example, $x=0.08$, in 400 nm to 800 nm region. Fig.2 is the magnetic and magneto-optical properties of PtFe/Co multilayers. 20% enhancement of polar Kerr rotation are obtained in PtFe/Co multilayers when $x=4.2\%$ at 400 nm wavelength⁸. It's assumed that the fluctuation of the Kerr rotation is due to the change of spin-polarization in PtFe spacer layers as a function of Fe doping content.

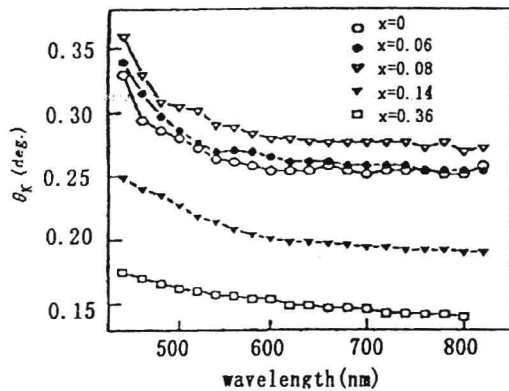


Fig. 1 The saturated polar Kerr rotation θ_K vs wavelength as the function of the doping concentration of Ni in the Pt spacer layer⁷.

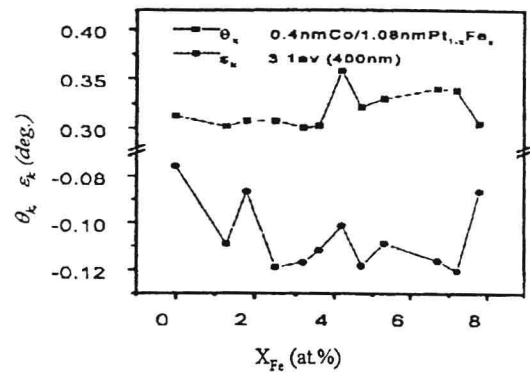


Fig.2 The magnetic and magneto-optical properties of PtFe/Co multilayers⁸.

Several years ago Al modified MnBiAl film was reported that the grain size was reduced to 40 nm, and Kerr rotation increased 2 degree at red wavelength, but no enhanced effect was found at blue wavelength. Now we can see from figure 3 that the Kerr rotation can be largely enhanced at short wavelength shows in Mn Bi_{0.47}Al_{0.15} film⁹. At photon energy of 3.3 eV, that is a wavelength of 376 nm, the remnant Kerr rotation is as large as 2.25 degree.

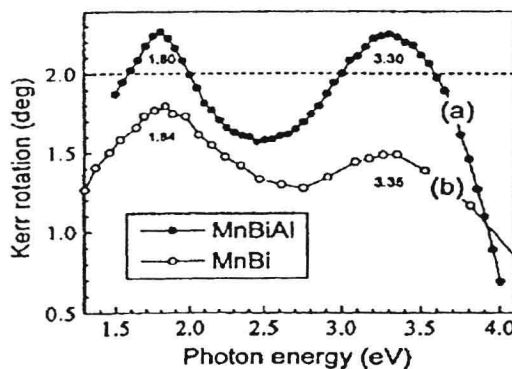


Fig. 3 The Kerr rotation spectrum of Mn Bi_{0.47}Al_{0.15} film⁹.

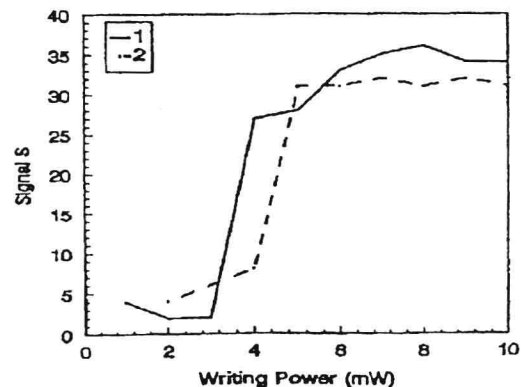


Fig. 4 The magneto-optical signal S of Bi, Ga, Cu doped DyIG film versus writing laser power for various laser duration times¹⁰.

Doping Cu to Bi, Ga substituted DyIG film can greatly increase the coercivity. The highest of 16 K Oe has been reported. At the same time, the film still has large rotation angle at 510 nm. Fig. 4 shows the magneto-optical signal S of Bi, Ga, Cu doped DyIG film versus writing laser power for various laser duration times. The wavelength of the laser is 514 nm. The solid line is for 600 ns writing pulse, the dashed lines for 250 ns. The reading power is 0.8 mW, reading pulse width 300 ns, applied bias field 400 Oe. This suggests the materials can be used for short wavelength optical storage¹⁰.

Phase change materials are promising rewritable optical storage materials. Great efforts have been made to push these materials to short wavelength recording¹¹. Different compounds have been used for short wavelength storage, such as Ge-Sb-Te system and Ag-In-Sb-Te system. $\text{Ge}_2\text{Sb}_2\text{Te}_5$ film owns high complex refractive change between crystalline state and amorphous state even in short wavelength. Fig. 5 shows the measured extinction coefficient of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ films annealed at different temperature¹¹. Fig. 6 shows the static optical storage performance of $\text{Ge}_2\text{Sb}_2\text{Te}_4$ film¹⁰. The wavelength of laser light is 514.5 nm. Large reflectivity contrast is obtained. $\text{Ag}_{13}\text{In}_{16}\text{Sb}_{33}\text{Te}_{36}$ film has a high refractive contrast at short wavelength but the write/erase cycle times are limited. $\text{Ag}_{14}\text{In}_{14}\text{Sb}_{35}\text{Te}_{23}$ has good erasability at short wavelength.

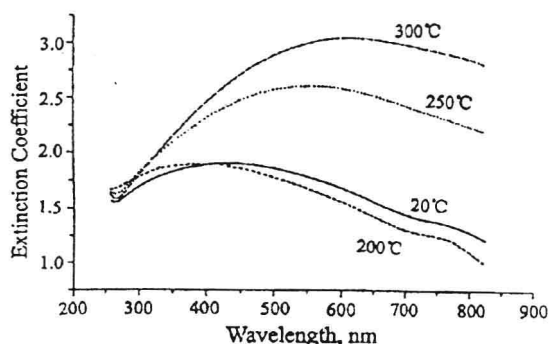


Fig. 5 The measured extinction coefficient of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ films annealed at different temperature¹¹.

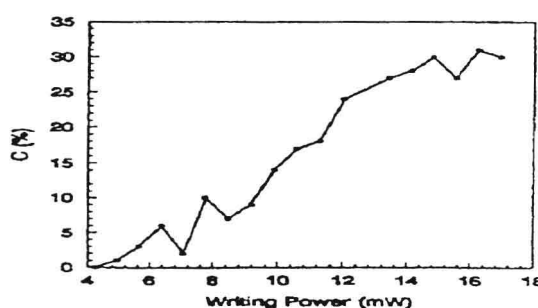


Fig. 6 The static optical storage performance of $\text{Ge}_2\text{Sb}_2\text{Te}_4$ film¹⁰.

The third kind high-density storage material is organic material, such as azo-dye materials¹¹. Fig. 7 shows the optical storage performance of a novel push-pull azo dye doped PMMA film prepared by spin coating method as a function of wavelength. The strong absorption of at around 500 nm is favorable to the use of the dye for optical storage at green laser wavelength. When the writing power is higher than 13.3 mW, a refractive contrast as high as 25% can be obtained.

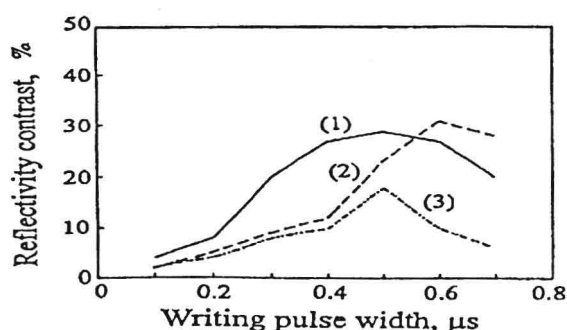


Fig. 7 The optical storage performance of azo dye doped PMMA film prepared by spin coating method¹¹.



Fig. 8 The STM image of an umbrella-like recorded pattern on CPU monomer thin film¹⁹.

3. NEAR FIELD OPTICAL STORAGE

The study on scanning near-field optical microscopy (SNOM) has been carried out in China for many years¹²⁻¹⁶. But study on the scanning near-field optical storage is the recent things. Several research groups in China are devoted into this field. A few fundamental works have been done. Simulation calculations for the energy transmission between the flying head and optical disc have been carried out¹⁷. Matrix solution of fiber-tapered wave-guide has been obtained¹⁸. Solid immersion lens have been designed and manufactured. Theoretical and experimental works on SUPER-RENS are under developed and being prepared. Super high-density storage by scanning tunneling microscope (STM) and atomic force microscope (AFM) has been reported. A novel organic compound, N-Cyano, N'-Phenyl, Urea (CPU) was synthesized and its thin film was prepared on highly ordered pyrolytic graphite substrate (HOPG)¹⁹. It was found that applying suitable voltage pulses between the tip and the thin film could form 0.8 nm recording marks in diameter. Fig. 8 shows the STM images of an umbrella-like recorded pattern on CPU monomer thin film obtained at $V_b=0.49V$, $I_t=0.57$ nA with a scanning rate of 0.2 Hz/image.

4. DIGITAL HOLOGRAPHIC STORAGE

Holographic storage possesses the characteristics of super high-capacity and super high data transfer rate. Many groups in China are devoted into this field. Their interests include holographic storage materials, such as LiNbO₃ photorefractive crystals doped or co-doped by different ions, azobenzene side-chain polymer with photoinduced anisotropy effect; volume holographic storage; holographic optical disk storage; nonvolatile holographic storage and so on.

As many as 1000 digital images have been recorded in a common volume of a Fe:LiNbO₃ photorefractive crystal using angular multiplexing²⁰. The combination of the error-correcting encoding and the differential encoding results in a significant noise-tolerant feature and thus a lower bit-error rate is achieved. This figure shows the schematic illustration of the experimental setup volume holographic storage in a Fe:LiNbO₃ crystal by using of angular multiplexing. 1000 digital images have been recorded in a common volume.

Some researchers are studying a different set of photorefractive materials for large-scale applications: photorefractive polymers. Photoinduced anisotropy and high-efficiency optical storage in azobenzene side-chain polymer have been studied²¹. Measurements reveal that the polymer possesses large magnitude of photoinduced birefringence ($\Delta n=7.8 \times 10^{-3}$). A reversible polarization hologram with high efficiency (19.3%) is recorded with a CW 532 nm laser in this thin film.

Several years ago a novel image parallel storage technique based on holographic optical disk storage theory was proposed. This is the parallel readout system of holographic optical disk. The parallel addressing/tracing technology has also been discussed in detail. Experimental disk-type 3-D holographic storage in a photorefractive crystal was reported by a team supervised by Prof. Tao last year²². 2000 high-resolution images have been stored in a disk-type photorefractive LiNbO₃:Fe crystal using spatioangular multiplexing with a spherical reference wave²³. They named it as spatioangularly multiplexed holographic disk (SAMHD). The holographic spots are allowed to overlap partially and to be distinguished from one another by use of different-angle reference beams. This strategy will simplify the optical storage setup, minimize the cross-

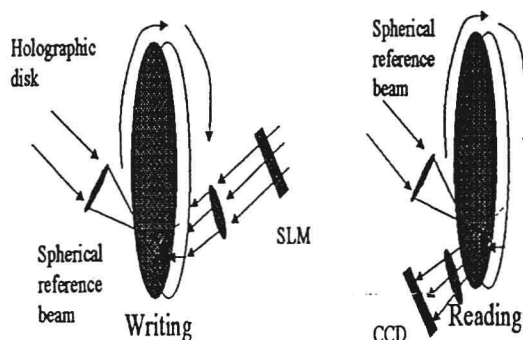


Fig. 9 The schematic diagram of SAMHD²².

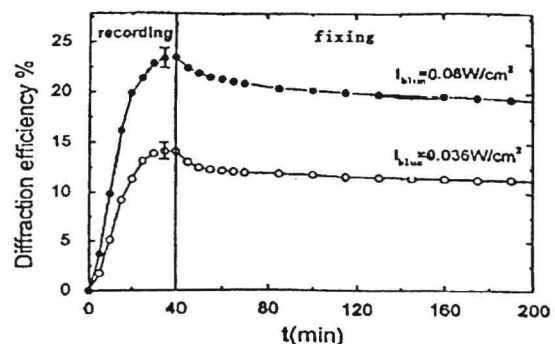


Fig. 10 The holographic recording and fixing characteristics of an oxidized LiNbO₃: Cu: Ce with blue-light-red-light scheme²⁵.

talk of adjacent tracks, improve the storage capacity and improve the diffraction efficiency. Fig. 9 is the schematic diagram of SAMHD. Recently multi-track storage of 10,000 holograms in a disk-type photorefractive crystal is studied. The disk contains 5 tracks²⁴.

One way to record holograms more permanently in LiNbO₃ is to "fix" them. A team from SIOFM have reported experimental and theoretical studies of Nonvolatile photorefractive holographic recording in LiNbO₃: Cu:Ce crystal with two illumination schemes²⁵: (1) UV light for sensitization and a red interfering pattern for recording and (2) blue light for sensitization and a red pattern for recording. Fig. 10 is the holographic recording and fixing characteristics of an oxidized LiNbO₃: Cu: Ce with blue-light-red-light scheme. The results show that the saturation diffraction efficiencies with the blue-light-red-light scheme are generally lower than those obtained with the UV-light-red-light scheme, the nonvolatile diffraction efficiencies are much higher for the blue-light-red-light scheme. It was also shown that there is an optimal red-to-blue intensity ratio for reaching maximum saturation and achieving the nonvolatile refractive-index modulation.

5. PHOTO-INDUCED MULTI DIMENSIONAL STORAGE

Photo-induced storage can be realized by different methods. These strategies have been studied by Chinese scientists: spectral hole-burning, photochromic effect, electron trapping, biology molecules, photo-induced nonlinear effect, two-photon absorption-based 3-D recording, 3 D data storage in glasses by fs laser.

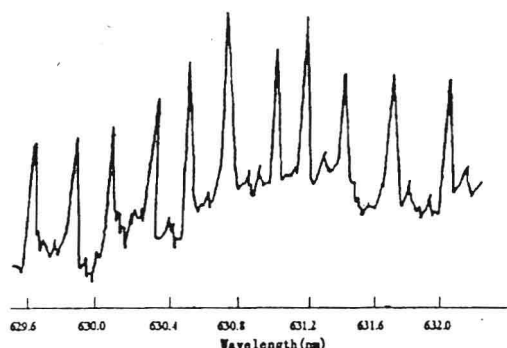


Fig. 11 The multiple photo-gated PHB of TZT/AC/PMMA²⁶

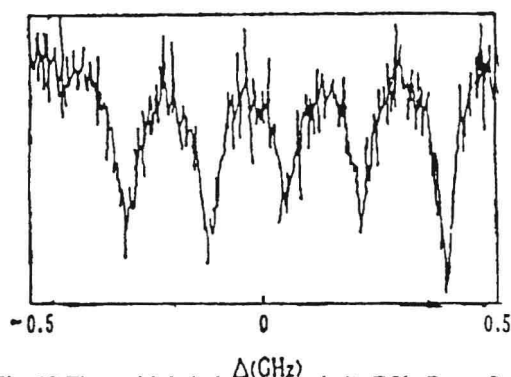


Fig. 12 The multiple hole-burning in BaFCl_{0.3}Br_{0.5}: Sm²⁺ at 2.3 K²⁶

Considerable work has been done in photo-gated spectral hole burning storage²⁶. Different kinds of materials have been designed and prepared. And the mechanisms have been studied. These materials include organic and inorganic systems, such as the derivative of Zn-tetraphenylporphyrin, TPTBPZn/aromatic cyanide AC/PMMA, 1000 holes can be burnt at 4.2K; ZntbP/CA/PhR, 155 holes were burnt at 20K; inorganic MyM¹-yFCl_xBr_{1-x}:Sm²⁺ system, M, M¹~ Ca, Mg, Ba, the $\Delta \nu_i$ is about 1000GHz and 5000 holes can be burnt at 2.3K; the first hole burning experiment at room temperature was realized in this system; Inorganic SrBa(SO₄)₂: Sm²⁺; microparticle based hole burning at room temperature and hole burning in Eu³⁺:Y₂SiO₅ crystal²⁷⁻²⁹. Fig. 11 shows the multiple photo-gated PHB of TZT/AC/PMMA. Fig. 12 is the multiple hole-burning in BaFCl_{0.3}Br_{0.5}: Sm²⁺ at 2.3 K. The central wavelength is 630 nm, and the scanning range is about 1 G Hz.

Photochromic storage is considered to have the potential to use in near field optical storage and 3D optical storage. Different kinds of photochromic recording compounds have been synthesized, such as spiropyran, fulgides, salicylidene-aniline and organometallic complexes²⁶. Recently, a multi-valued photochromic optical disk storage is carried out by static testing on pyrrole fulgide derivative film³⁰. Fig. 13 shows the static testing result of four-valued photochromic storage.

Electron trapping materials are a kind of novel erasable, rewritable optical storage media. These materials can trap and release electrons with input photons^{31,32}. They have also shown inestimable promise for use in optical computing and optical information processing fields because of their many attractive characteristics, such as high write/erase speeds (less than 5 ns), limitless erasability, multilevel digital recording, capable of 3 dimensional storage, high SNR, realizing optical storage and information processing at the same time³³. Many kinds of electron-trapping materials and electron trapping thin films are produced, such as Eu, Sm or Ce, Sm co-doped SrS or CaS. In these case, Ce ions were added as the dominant activators (luminescence centers)³⁴. Fig. 14 shows the recorded images in SrS:Eu, Sm-PMMA film. Multilayer volumetric storage